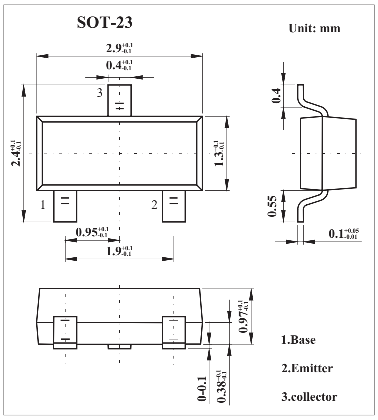
PNP Transistors

KST8550S



■ Features

● Collector current: I_{C}-=0.5A

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_{C}	-0.5	A
Collector Power Dissipation	P_{C}	0.3	W
Junction Temperature	T_{j}	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_{C}=-100 μ A, I_{E}=0	-40			V
Collector-emitter breakdown voltage	V_{CEO}	I_{C}=-1mA, I_{B}=0	-25			V
Emitter-base breakdown voltage	V_{EBO}	I_{E}=-100 μ A, I_{C}=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V, I_{E}=0			-0.1	μ A
Collector cut-off current	I_{CEO}	V_{CE}=-20V, I_{B}=0			-0.1	μ A
Emitter cut-off current	I_{EBO}	V_{EB}=-3V, I_{C}=0			-0.1	μ A
DC current gain	h_{FE}	V_{CE}=-1V, I_{C}=-50mA	120		350	
		V_{CE}=-1V, I_{C}=-500mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_{C}=-500mA, I_{B}=-50mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_{C}=-500mA, I_{B}=-50mA			-1.2	V
Transition frequency	f_{T}	V_{CE}= -6V, I_{C}= -20mA,f=30MHz	150			MHz

■ hFE Classification

Marking	2TY	
Rank	L	H
hFE	120～200	200～350

KST8550S

■Typical Characteristics

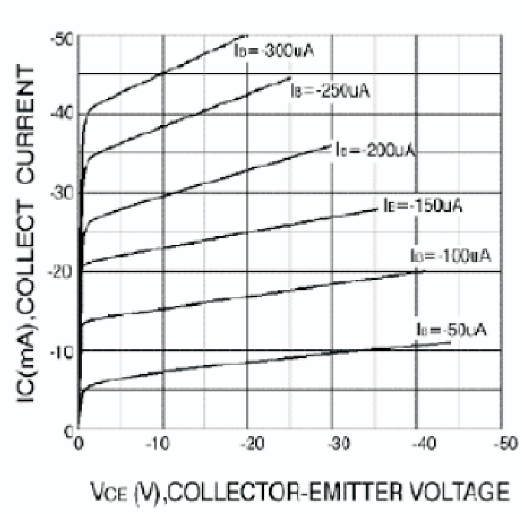


Fig.1 Static Characteristic

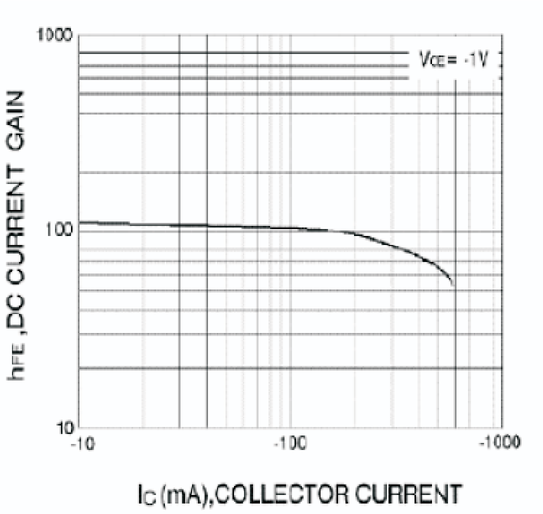


Fig.2 DC Current Gain

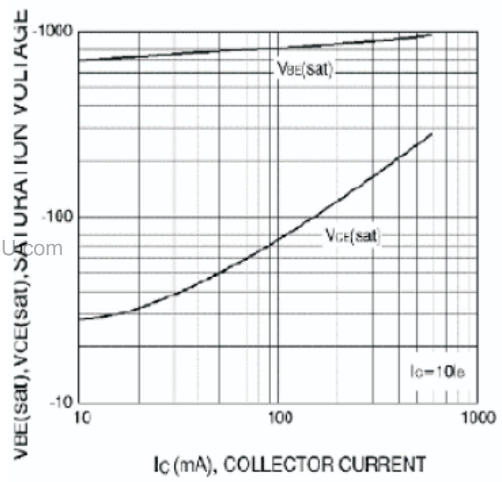


Fig.3 Bacse-Emitter Saturation Voltage

Collector-Emitter Saturation Voltage

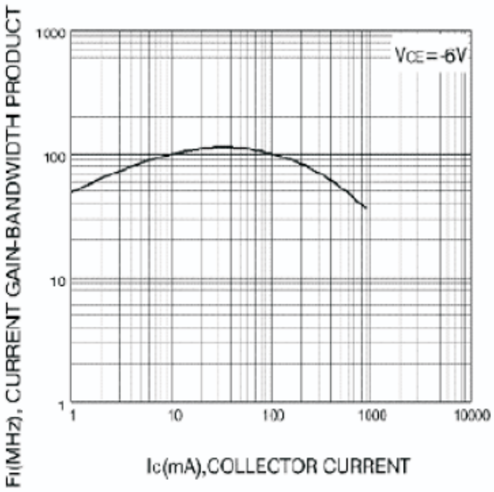


Fig.4 Current Gain Bandwidth Product